



# INTEL PC133 VALIDATION SPECIFICATION

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**Intel Corporation**

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## REVISION HISTORY

Revision	Draft/Changes	Date
1.03	IOH and IOL test Vcc condition from 3.0-3.6V to 3.0-3.45V	2/23/00

## 1.0 VALIDATION OVERVIEW

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The objective of the Intel PC133 validation program is to verify 133Mhz SDRAM compliance to the Intel PC133 specification and performance of DIMM modules in Intel reference systems, so as to provide a guidance of memory compatibility to Intel chipsets. The validation is conducted at two levels: component and system level. Intel will publish a list of validated PC133 SDRAM devices and DIMM modules on the web page.

Component level validation consists of device AC/DC/Functional tests and parasitic characterization. Device AC/DC/Functional tests include testing of critical parameters: tsi, thi, toh, tac, Vol, Voh, Iol, Ioh as well as Vcc and Vss clamp and I/O buffer I-V characteristics, while device parasitic characterization examines parasitic capacitance of input pins, data pins and clock pins.

System level validation verifies DIMM module's functionality and compatibility on Intel reference platforms over specification ranges with industry standard and Intel specific test software.

## 2.0 Test Methodology and Validation Sample Requirements

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### 2.1 AC/DC and Functional Test Methodology

#### 2.1.1 AC/DC and functional test conditions

Device AC/DC characteristics and functionality are tested to the PC133 specification limits as listed in [Table 1](#)

**Table 1. AC/DC/Functional test conditions**

Vdd	Vddq	Tc (device case temperature)
3.0V	3.0V	85C
3.6V	3.6V	85C
3.0V	3.0V	0C
3.6V	3.6V	0C

#### 2.1.2 AC/DC and functional test program flow

The DC electrical and AC timing tests are conducted on HP83000 or equivalent automatic testers. A list of patterns are also executed to confirm the device functionality and performance. The test program flow is summarized and described in [Table 2](#).

**Table 2. AC/DC/functional test program flow**

SEQUENCE	TEST	DESCRIPTION
1	Power up	Device power up and initialization

**Table 2. AC/DC/functional test program flow**

SEQUENCE	TEST	DESCRIPTION
2	Functional tests	March, March L/R, DQM patterns. Pass/fail at 133Mhz and 100Mhz
3	Tac / Toh	Data set up and hold time. March pattern. Measured at 12pf tester load and the result is converted to 50pf load
4	Tsi / Thi	input set up and hold time March and DQM patterns
5	Vih / Vil	Input voltage high / low March/DQM patterns at relaxed timing
6	Iccac	Active Icc. All banks open, ping-pong reads, BL=4, Measured at Vcc power supply
7	Ioh / Iol	DC test I/O buffer I-V characteristics Write FF for Ioh, 00 for Iol, then loop on read. Force voltage, measure current on DQ pins after settling time of 1us. For VDD = 3.45V, step forcing voltage from 3.45V to 0V with 0.2V interval. For VDD = 3.0V, step forcing voltage from 3.0V to 0V with 0.2V interval.
8	Vcc / Vss clamp	DC test Vcc / Vss clamp characteristics  VCC CLAMP test: Force voltage, measure current on CLK, CKE, CS, DQM, and DQ pins after settling time of 10 ms. For VDD = 3.6V, step forcing voltage from 3.6V to 5.6V with 0.2V interval. For VDD = 3.0V, step forcing voltage from 3.0V to 5.0V with 0.2V interval  VSS CLAMP test: Force voltage, measure current on CLK, CKE, CS, DQM, and DQ pins after settling time of 10 ms. For VDD = 3.6V, step forcing voltage from 0V to -2V with 0.2V interval. For VDD = 3.0V, step forcing voltage from 0V to -2V with 0.2V interval
9	END	

## 2.2 Parasitic test Methodology

Device parasitic capacitance is characterized with a HP8753ES Vector Network Analyzer. DUT is interfaced to test probe through a test fixture to allow ease of probing. The extra capacitance introduced by the test fixture is characterized and extracted from the final results. More information regarding detailed measurement set up is available from Intel.

The parasitic measurements are conducted under the conditions listed in [Table 3](#)

**Table 3. Parasitic test conditions**

Parameter	Value
Test Frequency	1Mhz
Probe Bias	1.4V with 200mV AC swing
Vcc	3.3V
Temperature	Room temperature

## 2.3 System tests

The System tests will be conducted under the conditions listed in [Table 4](#).

**Table 4. System test conditions**

Vcc	Ambient temperature	System loading
3.0V	55C	Heavy/light
3.6V	55C	Heavy/light
3.0V	25C	Heavy/light
3.6V	25C	Heavy/light

## 2.4 Validation sample requirements

Minimum validation sample requirement is summarized in [Table 5](#). Intel strongly recommends suppliers to submit device characterization data with validation samples for correlation purpose. Supplier should contact respective Intel account manager for validation sample submission.

**Table 5. Minimum validation sample requirement**

Validation Type	DRAM AC/DC/Functional	DRAM Parasitic	System
Sample Requirement	3 devices per configuration per density	2 devices per configuration per density	6 DIMMs per configuration per density
Recommended Data from Suppliers	Characterization data at Tcase = 0C, 85C and Vcc=3.0V, 3.6V, for min. of 2 devices	Parasitic data at room temperature for min. 1 device	TBD

## 3.0 PC133 Specification Validation Requirements (Component)

### 3.1 DC/AC/Functional validation

#### 3.1.1 DC Tests

DC parameters are tested to Intel PC133 specification as shown in [Table 6](#). Functional tests are performed with various patterns at different input voltages to determine compliance to spec.

**Table 6. D.C parameter tested**

Symbol	Parameter	Condition	Min	Max	Units	Notes
Iccac	Icc active	All banks open, initialize solid 1 and 0 pattern, ping-pong reads, BL=4, Measured at Vcc power supply		140/165 185	mA	16M/64M 128M/256M

**NOTE:** No Activate or Precharge currents should be included in the Iccac value.

#### 3.1.2 AC Tests

AC parameters are tested to Intel PC133 specification as shown in [Table 7](#). Functional tests are performed with various patterns at different input voltages.

**Table 7. AC parameter tested**

Symbol	Parameter	Condition	Min	Max	Units	Notes
Vih	Input High Voltage	Functional pass/fail	2.0	VDDQ+2.0	V	
Vil	Input Low Voltage	Functional pass/fail	VSSQ – 2.0	0.8	V	

AC timing parameters listed in [Table 8](#) are tested under the conditions specified in section 2.1.1. Test result must meet Intel PC 133 specification limits. Functional tests will be performed at 133Mhz and 100Mhz to guarantee device compatibility with PC100.

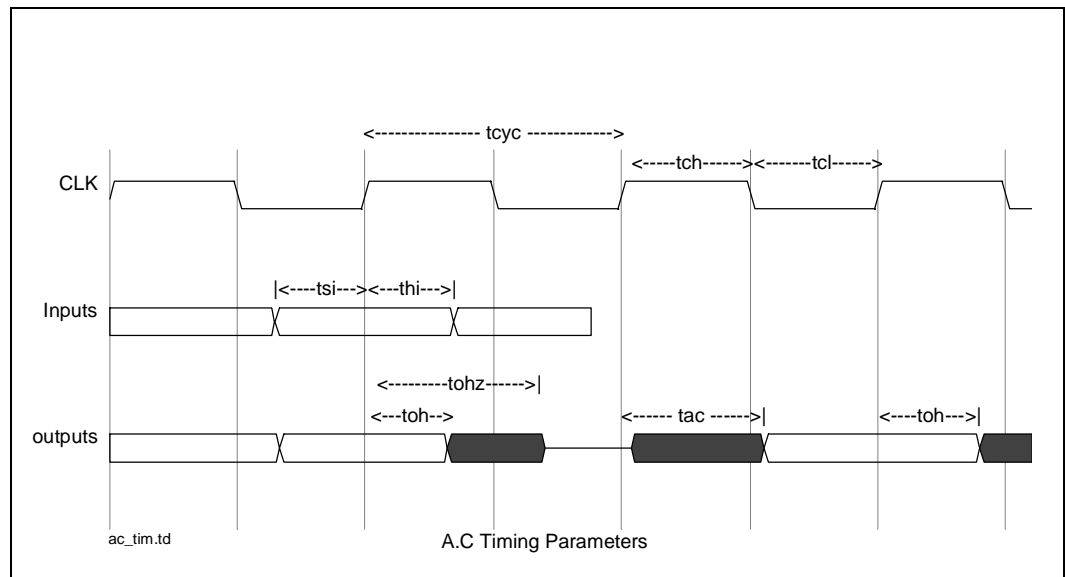
The correlation between load condition of HP83000 tester and that of PC133 specification condition are thoroughly investigated. A correction factor of 0.7ns and 0.6 ns is determined for Tac and Toh respectively. For a more detailed experiment report, see Appendix B.

**Table 8. 133/100/66 MHz AC Timing Parameters For  $C_L=2$  and 3**

Parameter	Symbol	Speed Grade 66 MHz		Speed Grade 100 MHz		Speed Grade <sup>1</sup> 133MHz		Unit	Notes
		Min	Max	Min	Max	Min	Max		
Input Setup Times	Tsi	3		2		1.5		ns	
Input Hold Times	Thi	1.5		1		0.8		ns	
Output Valid From Clock	Tac		9		9		5.4	ns	
Output Hold From Clock	Toh	3		3		3		ns	Note 1
RAS# Active Time	Tras	5		5		6		Tclk	Functional test Note 2
Activate to Command Delay (RAS# to CAS# Delay)	Trcd	2		3/2		3/2		Tclk	Functional test Note 2
RAS# Precharge Time	Trp	3/2		3/2		3/2		Tclk	Functional test Note 2
Clock	Clk	3/2		3/2		3/2			Functional test Note 2

**NOTE:**

1. For 133MHz, either 3.0ns @ 50pF needs to be met with I/V curve, or 1.8ns @ 0pF needs to be guaranteed.
2. The parameter needs to be retested @ 100MHz to guarantee compatibility with PC100.

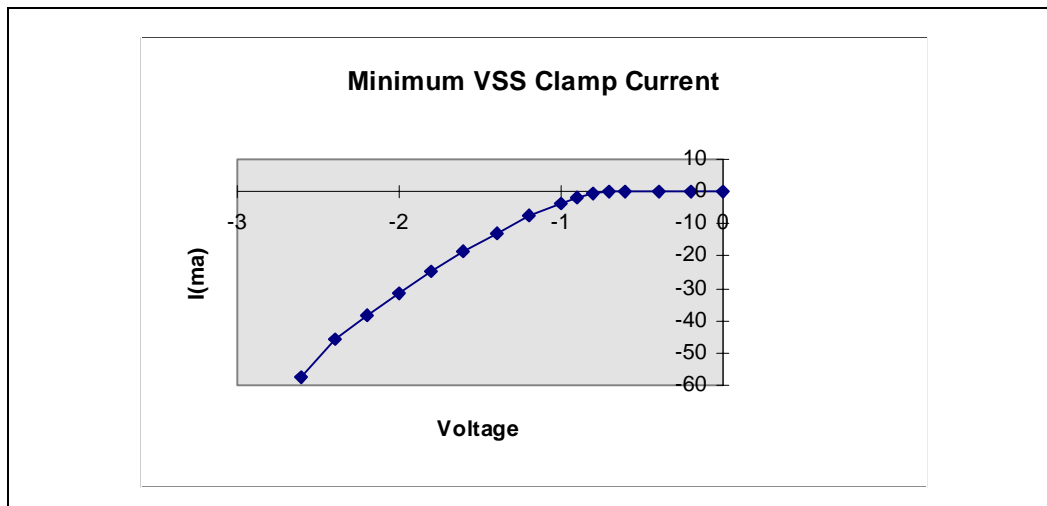
**Figure 1. A.C Timing Parameters**


### 3.1.3 I/V Characteristics for Input and Output Buffers

#### 3.1.3.1 Vss and Vcc clamp characteristics

Vss and Vcc clamp characteristics are tested for CK, CS, DQMB, DQ and CKE pins and are described in Figure 2 and Figure 3. Table 9 and Table 10 list the maximum (minimum in absolute value) and minimum required current levels at respective Vss and Vcc.

Figure 2. SDRAM VSS Clamp Characteristics



**NOTES:**

1. Required for CK, CS, DQMB, DQ and CKE pins.
2. This data is referenced to the ground.
3. Must meet the temperature and voltage range specified above.
4. This drawing is not to scale. Comparisons should be made to the data table provided.

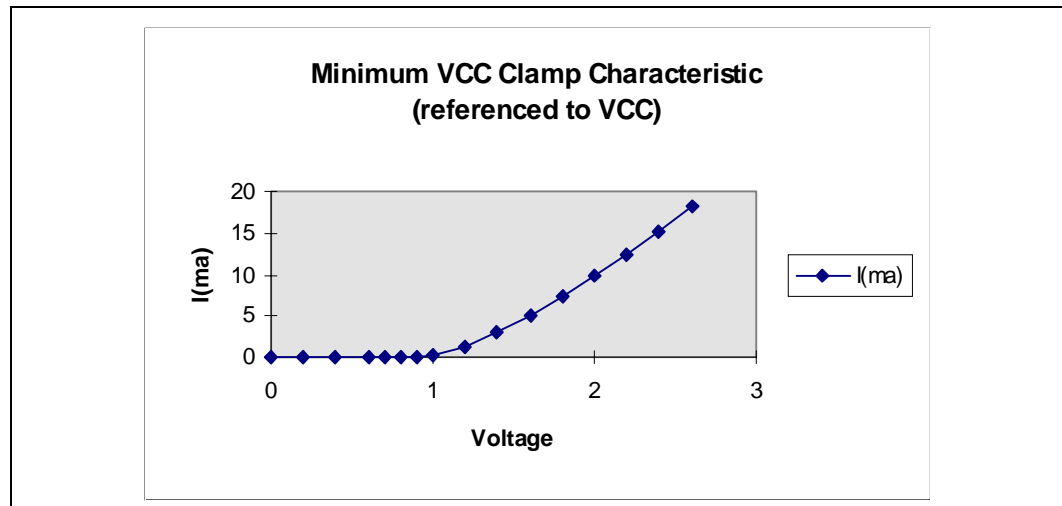
Table 9. Data Points For Figure 2

VSS	I (mA) (Max)
-2.6	-57.23
-2.4	-45.77
-2.2	-38.26
-2	-31.22
-1.8	-24.58
-1.6	-18.37
-1.4	-12.65
-1.2	-7.57
-1	-3.37
-0.9	-1.75
-0.8	-0.58
-0.7	-0.05



**Table 9. Data Points For Figure 2**

-0.6	0
-0.4	0
-0.2	0
0	0

**Figure 3. SDRAM Vcc Clamp Characteristics**

**NOTES:**

1. Required for CK, CS, DQMB, DQ and CKE pins.
2. This data is referenced to the VCC voltage.
3. Must meet the temperature and voltage range specified above.
4. This drawing is not to scale. Comparisons should be made to the data table provided.

**Table 10. Data Points For Figure 3**

VCC	I(ma) (Min)
2.6	18.31
2.4	15.3
2.2	12.48
2	9.83
1.8	7.35
1.6	5.06
1.4	3.02
1.2	1.34
1	0.23
0.9	0
0.8	0

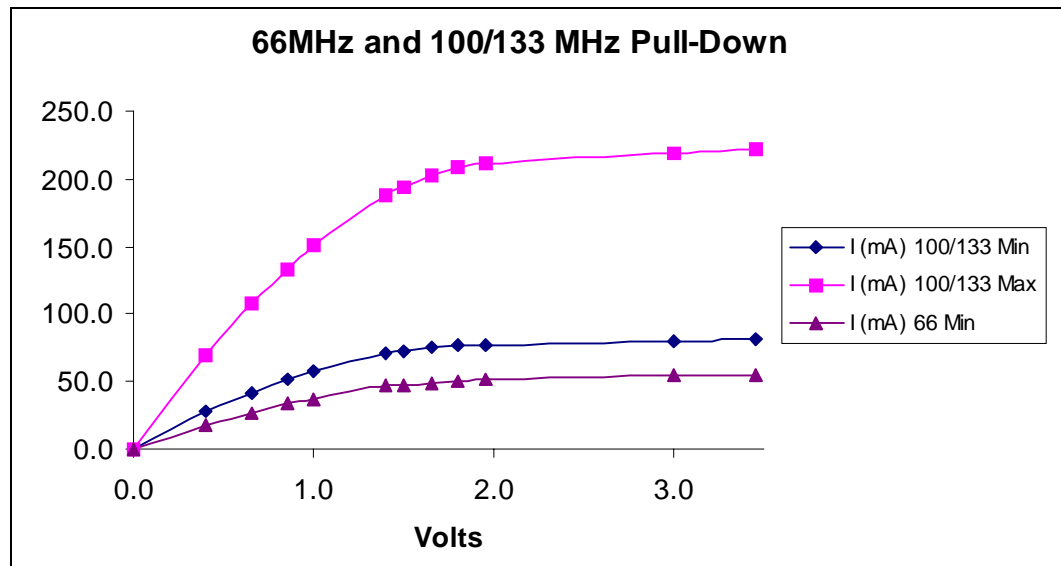
**Table 10. Data Points For Figure 3**

0.7	0
0.6	0
0.4	0
0.2	0
0	0

### 3.1.3.2 I/O Buffer Characteristics

I/O buffer pull-down and pull-up characteristics are described in Figures 4 and 5. I-V characteristics are determined for all DQ pins in the voltage range specified in Table 11 and Table 12. The test results must be within the specification ranges.

**Figure 4. SDRAM DQ Output Buffer Pull-Down Characteristics (Vcc= 3.0-3.45V)**



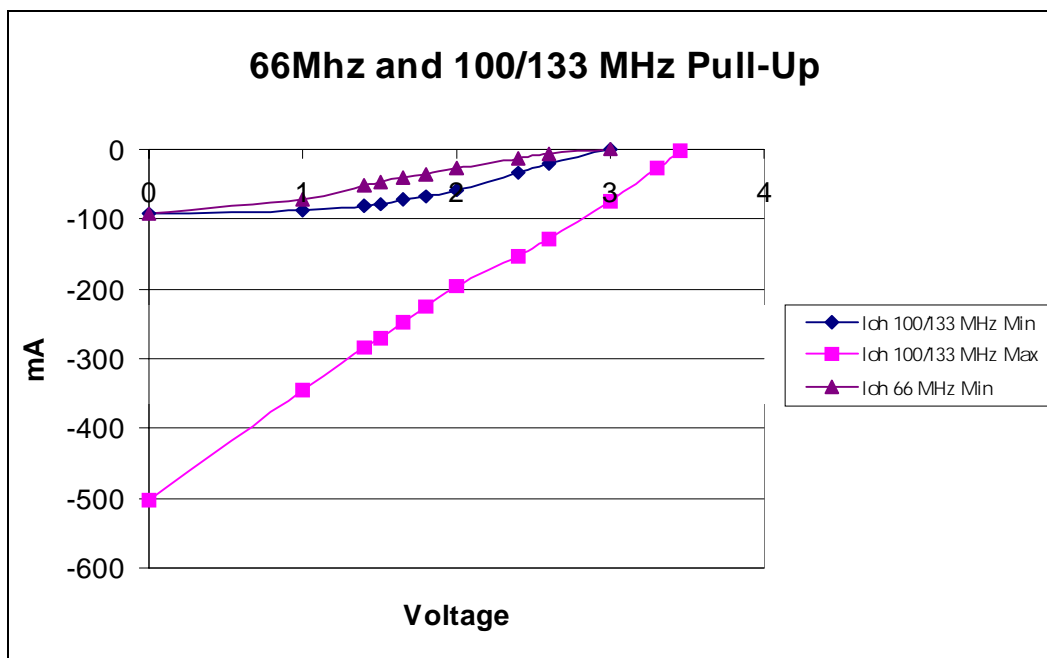
**NOTES:**

1. Must meet the temperature and voltage range specified above.
2. This drawing is not to scale. Comparisons should be made to the data table provided.

**Table 11. Data Points For Figure 4**

Pulldown			
Voltage (V)	I (ma)	I (ma)	I (ma)
	100/133MHz min	100/133MHz Max	66 MHz min
0	0.0	0.0	0.0
0.4	27.5	70.2	17.7
0.65	41.8	107.5	26.9
0.85	51.6	133.8	33.3
1	58.0	151.2	37.6
1.4	70.7	187.7	46.6
1.5	72.9	194.4	48.0
1.65	75.4	202.5	49.5
1.8	77.0	208.6	50.7
1.95	77.6	212.0	51.5
3	80.3	219.6	54.2
3.45	81.4	222.6	54.9

Figure 5. SDRAM DQ Output Buffer Pull-Up Characteristics (Vcc= 3.0-3.45V)



**NOTES:**

1. Must meet the temperature and voltage range specified above.
2. This drawing is not to scale. Comparisons should be made to the data table provided.

Table 12. Data Points For Figure 5

Pullup			
Voltage	100/133 MHz min	100/133 MHz max	66 MHz min
(V)	I(ma)	I(ma)	I(ma)
3.45		-2.4	
3.3		-27.3	
3	0	-74.1	-0.7
2.6	-21.1	-129.2	-7.5
2.4	-34.1	-153.3	-13.3
2	-58.7	-197	-27.5
1.8	-67.3	-226.2	-35.5
1.65	-73	-248	-41.1
1.5	-77.9	-269.7	-47.9
1.4	-80.8	-284.3	-52.4
1	-88.6	-344.5	-72.5
0	-93	-502.4	-93

## 3.2 Device Parasitic validation

Device parasitics capacitance is characterized for all input pins, I/O pins and clock pins. The test conditions and specification limits are summarized in [Table 13](#).

**Table 13. Parasitic capacitance tests**

Symbol	Parameter	Condition	Min	Max	Units	Notes
Cin	Input Pin Capacitance	@ 1 MHz, 23°C Tj, 1.4v bias, 200mv swing, Vcc=3.3v	2.5	3.8	pF	Target 3.15pf
CI/O	I/O Pin Capacitance	@ 1 MHz, 23°C Tj, 1.4v bias, 200mv swing, Vcc=3.3v	4.0	6.5	pF	Target 4.8pf
Cclk	Pin Capacitance	@ 1 MHz, 23°C Tj, 1.4v bias, 200mv swing, Vcc=3.3v	2.5	3.5	pF	Target 3.0pf

## 4.0 System Level Validation (DIMM Modules)

DIMM module's functionality and compatibility are validated on Intel reference platforms with industry standard and Intel specific test software. The test conditions are specified in section 2.1.3. DIMM modules must be assembled with validated PC133 SDRAM components.

## Appendix A

### Output Load Specification

Access times for 66 MHz, 100 MHz and 133MHz SDRAM devices are specified into a 50pf load only, without resistive termination.

Applications which are being simulated and implemented **do not** have a resistive termination.

Both Tac and Toh specifications are simulated based on the following:

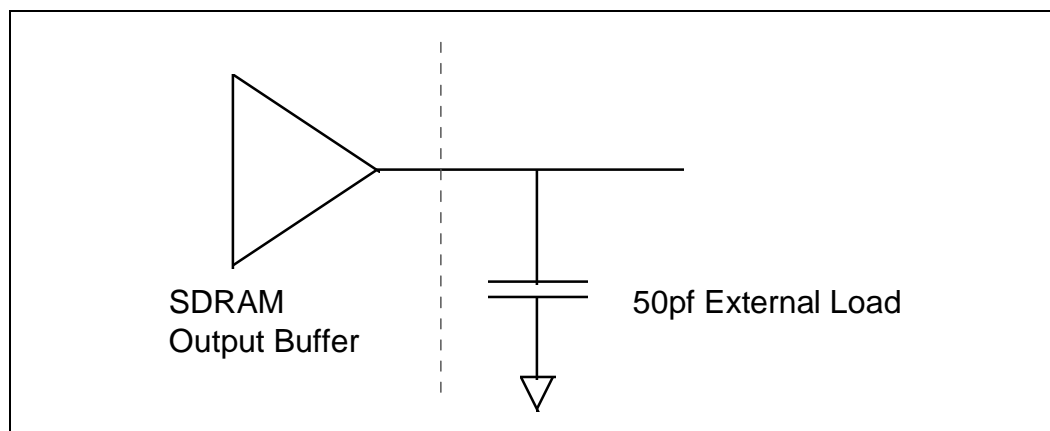
	66 MHz	100 MHz	133 MHz	Load
Tac	9ns	6ns	5.4ns	50pf
Toh	3ns	3ns	3ns	50pf

**NOTES:**

1. @ Vcc= 3.0v to 3.6v
2. @ Ta= 0C to 65C

If test conditions other than 50pf capacitive load are used, then the proper correlation factor should be used for your specific test condition.

**Figure 6. Output Load Circuit**



## Appendix B

### HP83K F330 Tester Correction Factor Study for AC Timing

#### Background

PC SDRAM Specification states the following for AC timing at 133Mhz:

$T_{ac} = 5.4 \text{ ns @ } 50\text{pf}; \text{ or } 4.6 \text{ ns @ } 0\text{pf}$

$T_{oh} = 3.0 \text{ ns @ } 50\text{pf}; \text{ or } 1.8 \text{ ns @ } 0\text{pf}$

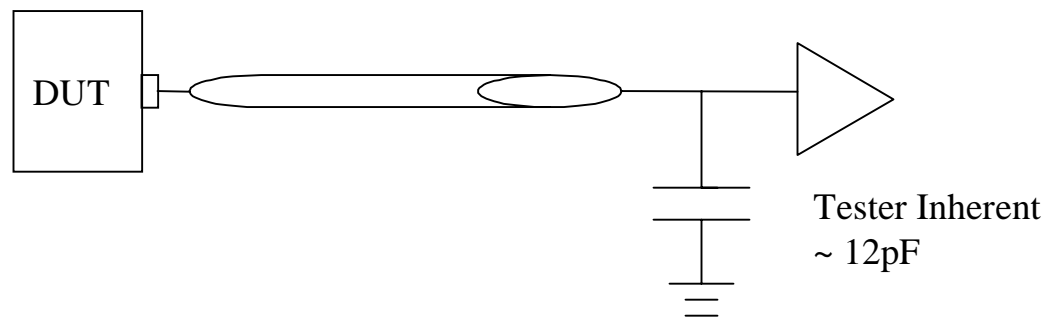
$T_{ac}$  and  $T_{oh}$  can be measured using a HP83K F330 Tester. However, the tester environment has about 12pf of total loading capacitance. The measured data need to be corrected to be interpreted at 50pf. This document details the methods and data collected in order to determine the tester correction factors.

#### Experiment

A 64Mbit (8Mx8) 133Mhz device was soldered down on a Ideal Logic SMT002-01A load board. AC timing was measured with device looping in read cycle.

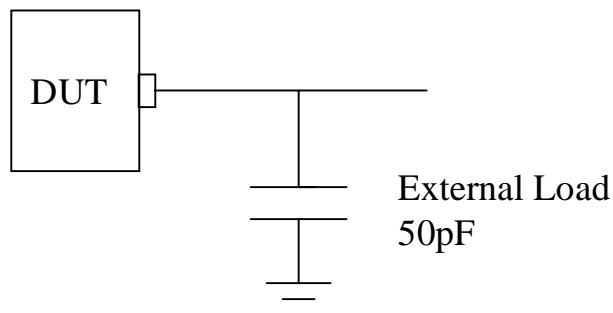
First, HP83000F330 tester was used to measure  $T_{ac}$  and  $T_{oh}$  using binary search. An auto calibration routine was performed to calibrate out the intrinsic parasitic effect resulted from the load board, socket and transmission lines. Therefore, the AC timing measured by HP83K is only affected by a total capacitance load of 12pf from the tester comparator. The tester comparator is set at 1.5V. The test set up is illustrated in Figure 1.

**Figure 1. HP 83K F330 Test Set Up**



Then, the AC timing of the same device was measured using a Tektronix TDS784 oscilloscope and active probes P6245 without any external capacitance. The trace capacitance on this set up, which included the active probes, the jumper and the transmission lines, is approximately 13pf.

The measurements on the scope were repeated by adding an external capacitance of 50pf. The test set up is illustrated in Figure 2.

**Figure 2. Oscilloscope Test Set Up**

**Experimental Data**

The AC timing data for 4 pins at room temperature, 3.3V Vcc are listed in Table 1.

**Table 1. AC timing data**

	Oscilloscope				HP83K F330	
	load: trace cap		load: trace+50pf		load: 12pf	
Pin	Tac (ns)	Toh (ns)	Tac (ns)	Toh (ns)	Tac (ns)	Toh (ns)
DQ0	4.3	4.1	5.2	4.8	4.11	3.93
DQ3	4	3.8	4.9	4.6	3.92	3.56
DQ4	3.9	3.8	4.9	4.6	3.92	3.58
DQ7	4.3	4	5.1	5	4.08	3.65

**Data Analysis and Results**

Under the setup conditions in this experiment, AC timing has a linear relationship with the capacitance load. This can be derived mathematically:

$$V = V_{oc}e^{-t/RC}$$

V, Vo and R are held constant  $\Rightarrow$

$$t \propto RC$$

$$\Delta t \propto \Delta C$$

Since the device was tested at 12pf on HP83K, to interpret the values at 50pf the following correction factors are computed:

$$T_{ac} = +0.7ns$$

$$T_{oh} = +0.6ns$$



As a result, the HP83K measured data should be corrected as shown in Table 2:

**Table 2. Measured vs. Interpreted Value**

Pin	HP83K Measured		Interpreted @ 50pf	
	Tac (ns)	Toh (ns)	Tac (ns)	Toh (ns)
DQ0	4.11	3.93	4.81	4.53
DQ3	3.92	3.56	4.62	4.16
DQ4	3.92	3.58	4.62	4.18
DQ7	4.08	3.65	4.78	4.25

